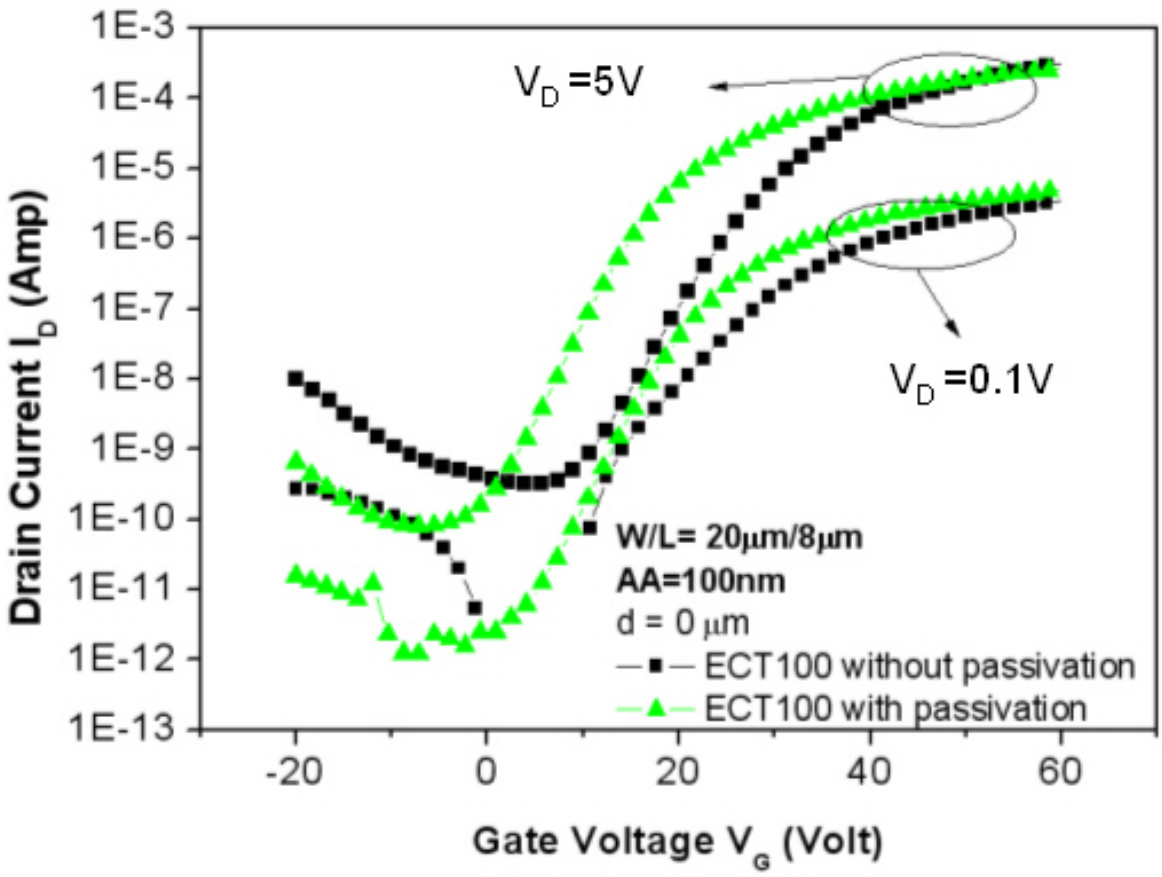

Figure 2-20 Transfer characteristics for ECT TFT's before and after 1hr NH_3 plasma passivation

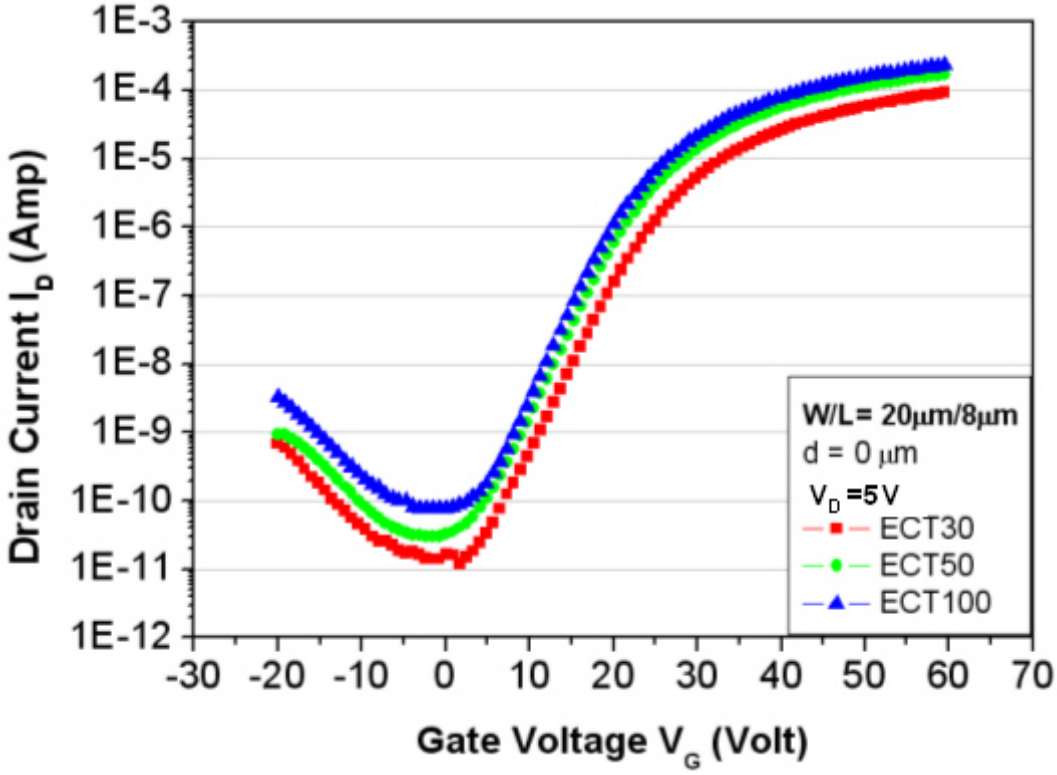

Figure 2-21 I_D - V_{GS} curves of ECT structure with different thickness of the active layer after passivation

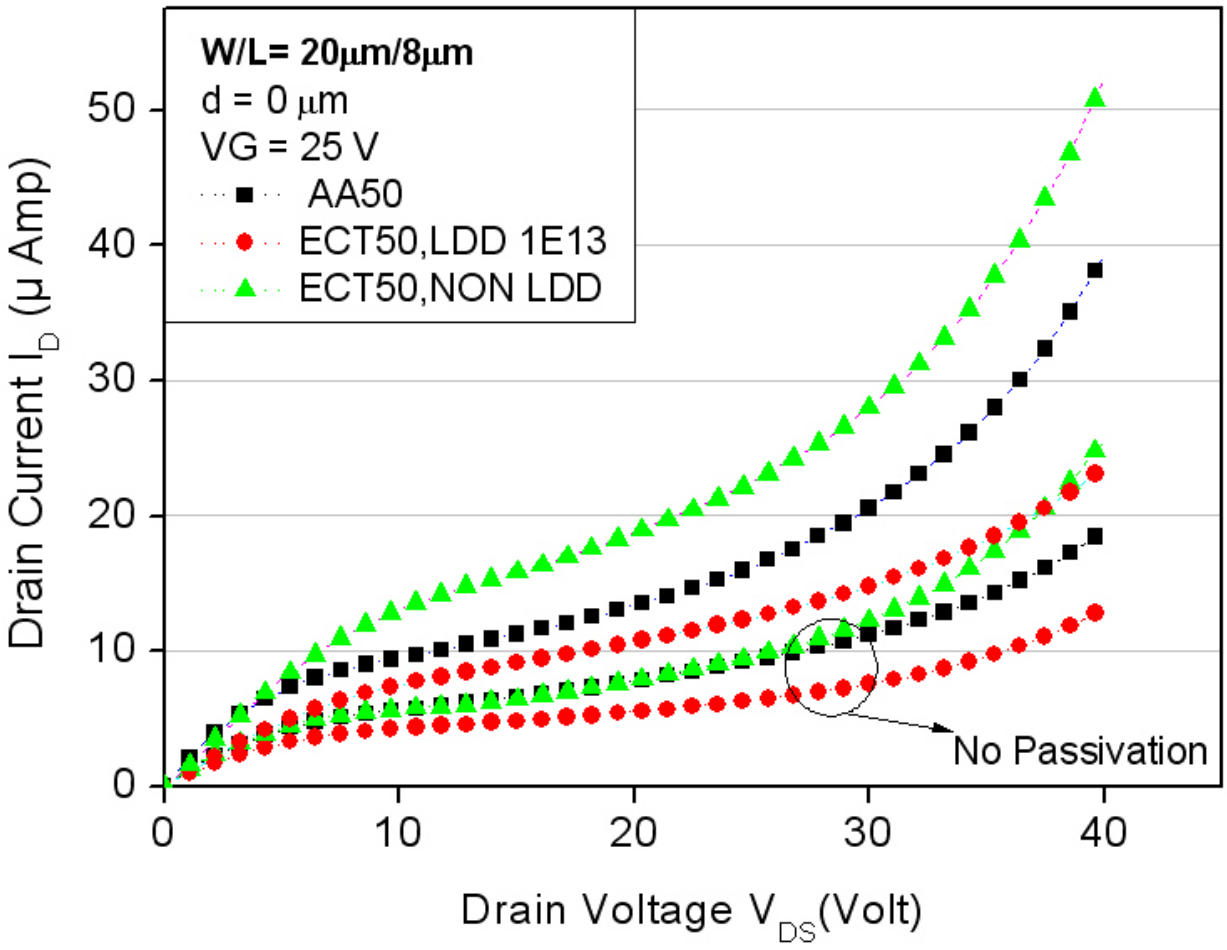

Figure 2-22 I_D - V_D curves extracted at V_G = 25 V for various TFT samples, before and after 1hr NH_3 plasma passivation

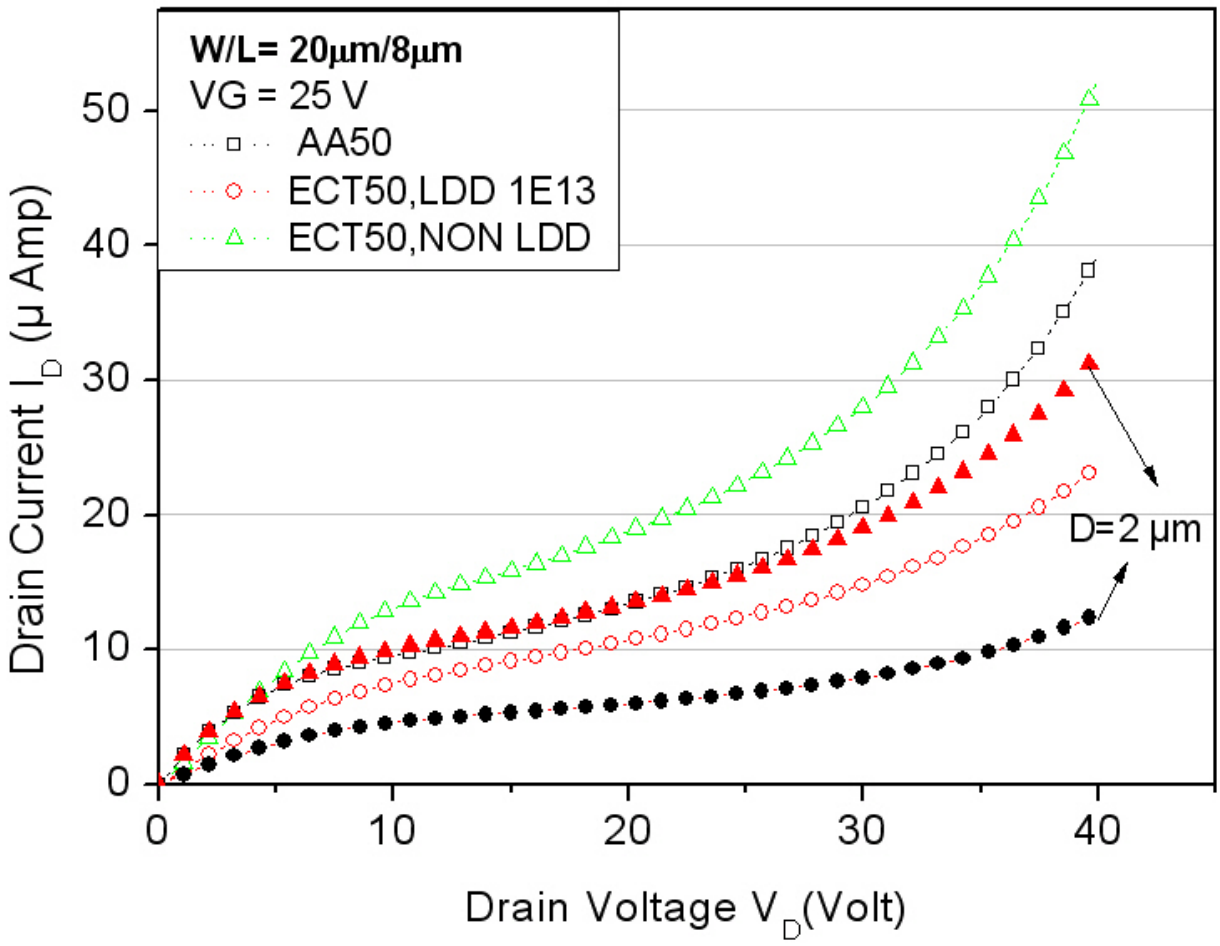

Figure 2-23 I_D - V_D curves extracted at V_G = 25 V for various TFT samples: (a) W/L = 20/8, d = 0 µm, and d = 2 µm, after 1hr NH_3 plasma passivation

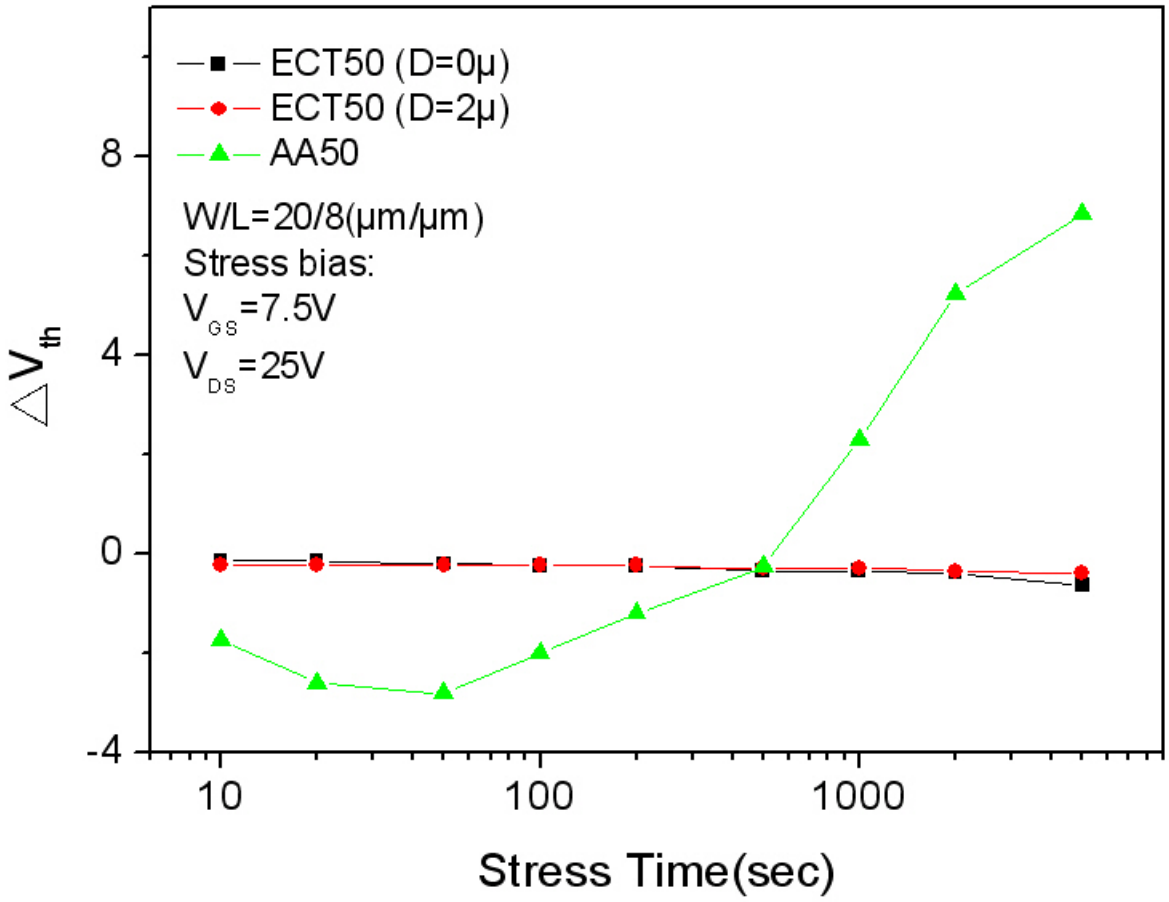

Figure 2-24 Variation of threshold voltage at V_{DS}=5V under hot carrier stress. D is gate overlapping length.

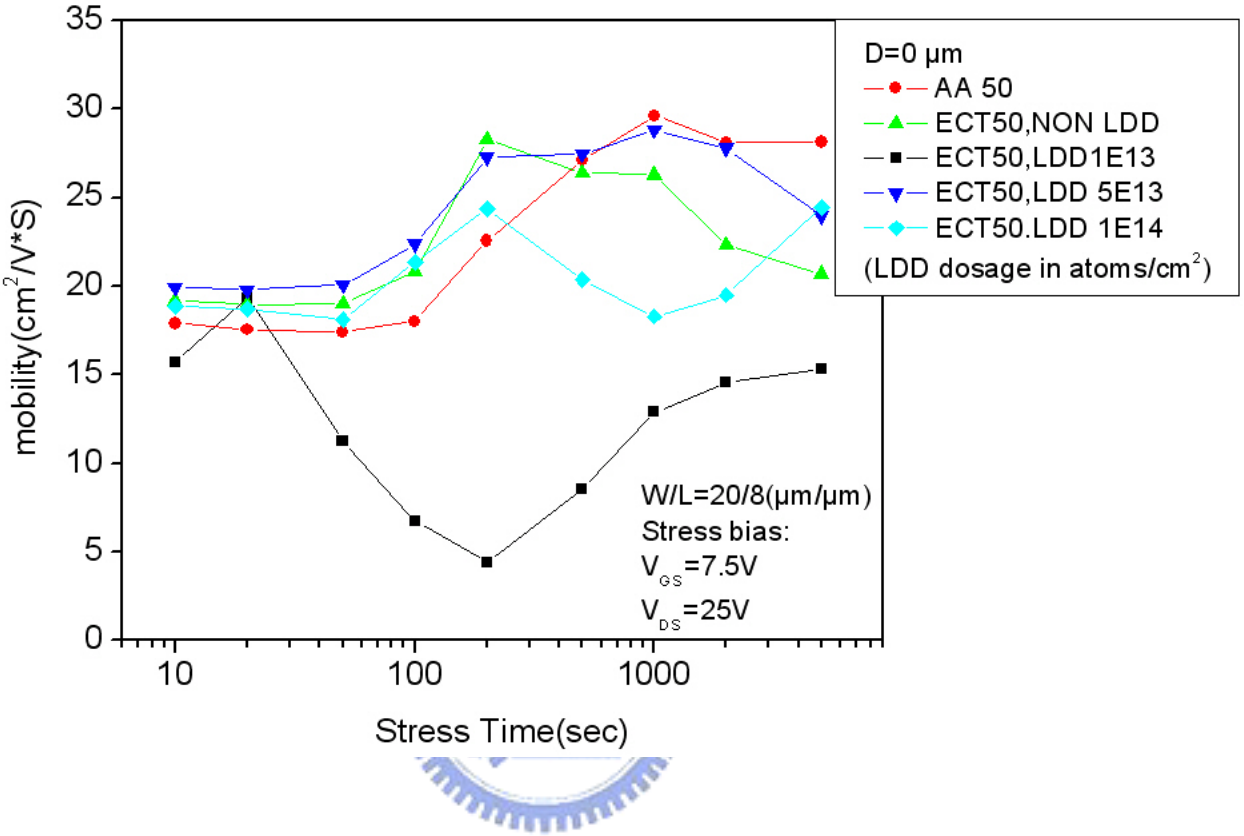

Figure 2-25 Variation of mobility at V_{DS}=0.1V under hot carrier stress.

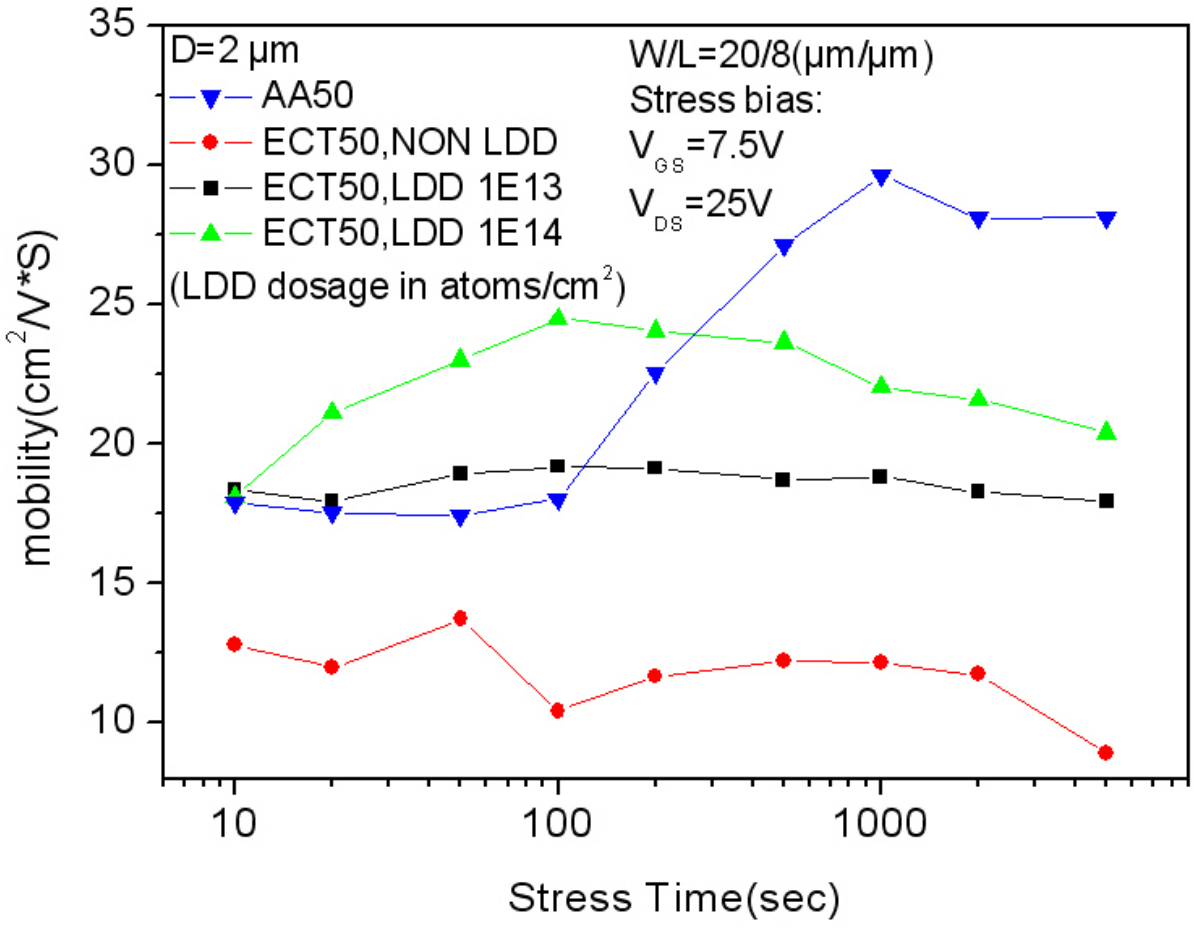

Figure 2-26 Variation of mobility at V_{DS}=0.1V under hot carrier stress.D(=2) is gate overlapping length.

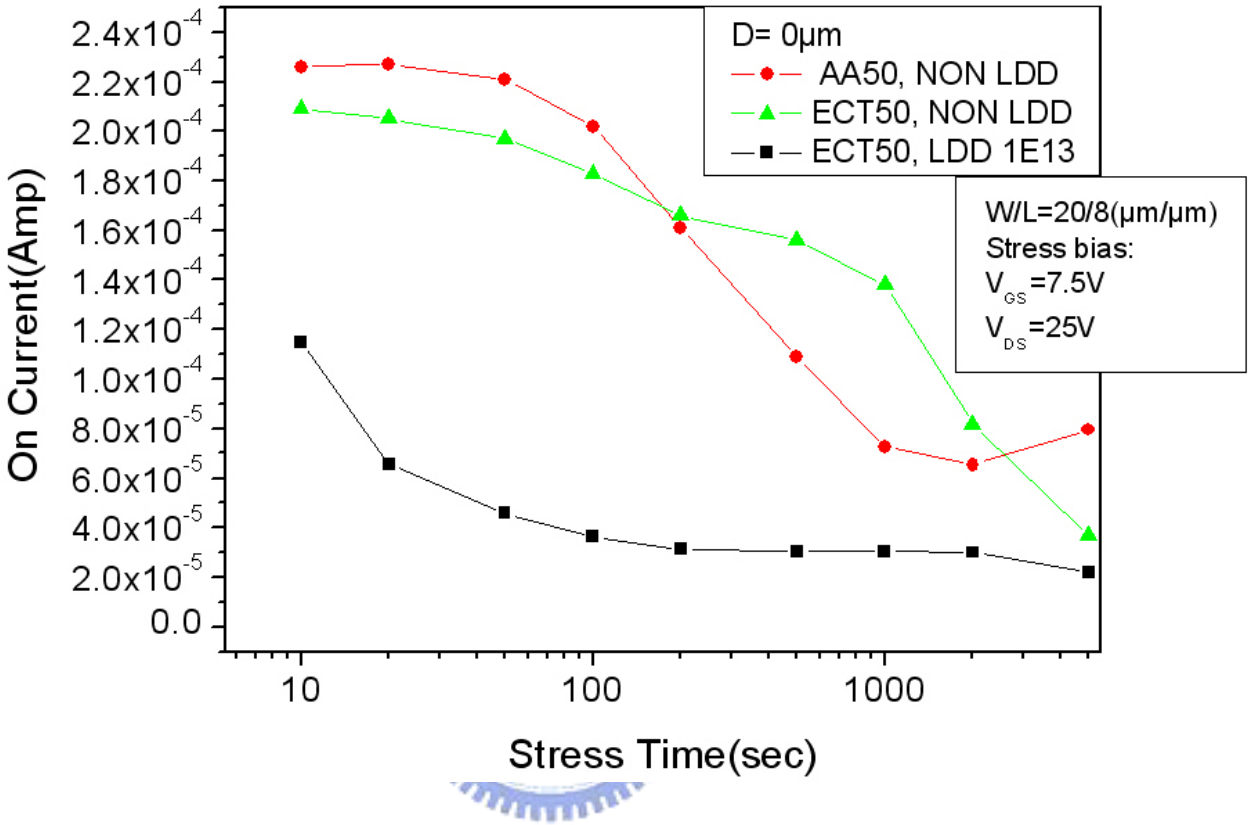

Figure 2-27 Variation of on current at V_{DS}=5V under hot carrier stress.

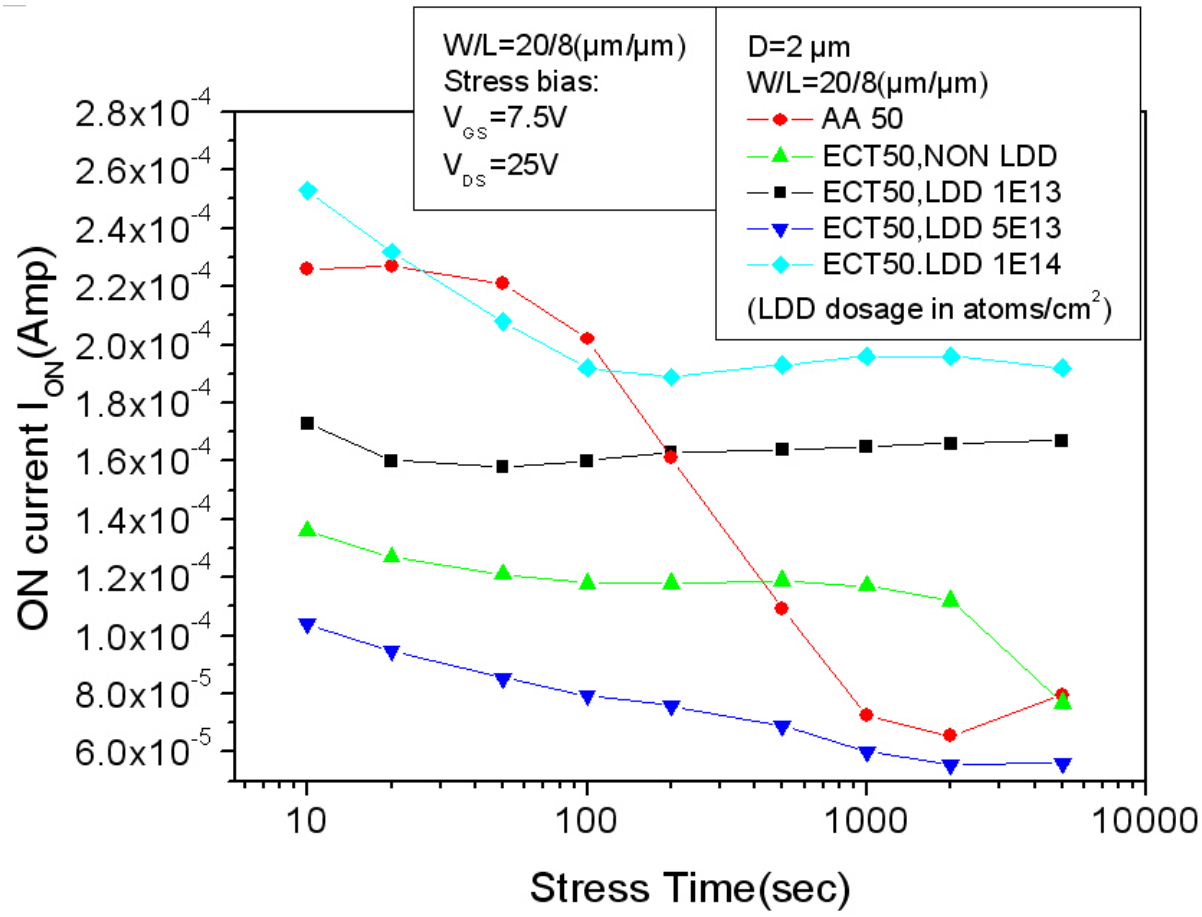

Figure 2-28 Variation of on current at V_{DS}=5V under hot carrier stress. D(=2) is gate overlapping length.